

# SIDC09D60F6

### Fast switching diode

#### Features:

- 600V Emitter Controlled technology 70 μm chip
- soft , fast switching
- low reverse recovery charge
- small temperature coefficient

#### This chip is used for:

 power modules and discrete devices



#### **Applications:**

SMPS, resonant applications, drives

Chip Type	$V_{R}$	I <sub>F</sub>	Die Size	Package
SIDC09D60F6	600V	30A	3 x 3 mm <sup>2</sup>	sawn on foil

#### **Mechanical Parameters**

Mechanical Faranieters			
Raster size	3 x 3		
Area total	9	mm <sup>2</sup>	
Anode pad size	2.518 x 2.518		
Thickness	70	μm	
Wafer size	150	mm	
Max. possible chips per wafer	sible chips per wafer 1612		
Passivation frontside	Photoimide		
Pad metal	3200 nm AlSiCu		
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bond		
e bond Electrically conductive glue or solder			
Wire bond	Al, ≤250μm		
Reject ink dot size	Ø 0.65mm; max 1.2mm		
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C		



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#### **Maximum Ratings**

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$	T <sub>vj</sub> = 25 °C	600	V
Continuous forward current	I <sub>F</sub>	<i>T</i> <sub>vj</sub> < 150°C	1)	A
Maximum repetitive forward current	I <sub>FRM</sub>	<i>T</i> <sub>vj</sub> < 150°C	60	] ^
Junction temperature range	$T_{vj}$		-40+175	°C
Operating junction temperature	T <sub>vj</sub>		-40+150	°C
Dynamic ruggedness <sup>2)</sup>	P <sub>max</sub>	$I_{\text{Fmax}} = 60\text{A}, V_{\text{Rmax}} = 600\text{V},$ $T_{\text{vj}} \le 150^{\circ}\text{C}$	tbd	kW

<sup>1)</sup> depending on thermal properties of assembly

#### **Static Characteristic** (tested on wafer), $T_{vj}$ = 25 °C

Parameter	Symbol	Conditions	Value			Unit
raiailletei	Syllibol	Conditions	min.	typ.	max.	Ullit
Reverse leakage current	$I_{R}$	V <sub>R</sub> =600V			27	μA
Cathode-Anode breakdown Voltage	$V_{BR}$	I <sub>R</sub> =1.5mA	600			V
Diode forward voltage	V <sub>F</sub>	/ <sub>F</sub> =30A		1.6		V

#### **Further Electrical Characteristics**

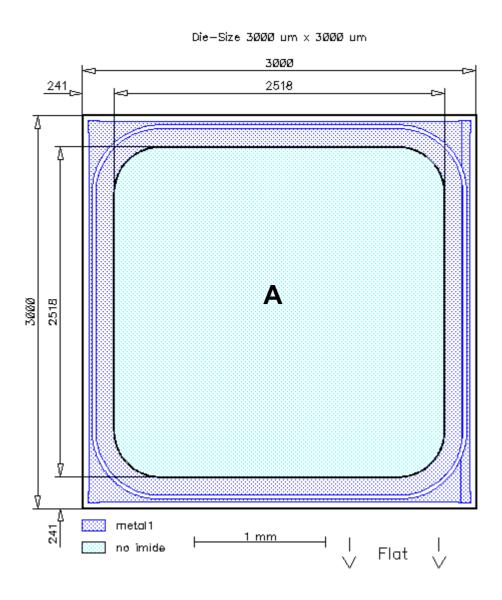
Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

<sup>&</sup>lt;sup>2)</sup> not subject to production test - verified by design/characterisation





#### **Chip Drawing**



### A: Anode pad



## SIDC09D60F6

#### **Description**

AQL 0,65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

#### **Revision History**

Version	Subjects (major changes since last revision)	Date
2.2	Max. possible chips per wafer change to 1612 pcs	03.09.2010

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